(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization

International Bureau



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(43) International Publication Date 6 May 2004 (06.05.2004)

PCT

(10) International Publication Number WO 2004/037713 A1

(51) International Patent Classification7:

B81C 1/00

(21) International Application Number:

PCT/IB2003/004586

- (22) International Filing Date: 17 October 2003 (17.10.2003)
- (25) Filing Language:

English

(26) Publication Language:

English

- (30) Priority Data: 02079467.3
- 24 October 2002 (24.10.2002) EF
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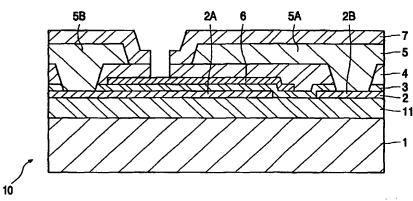
- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,

[Continued on next page]

(54) Title: METHOD FOR MANUFACTURING A MICRO-ELECTROMECHANICAL DEVICE AND MICRO-ELECTROMECHANICAL DEVICE OBTAINED THEREWITH



(57) Abstract: The invention relates to a method of manufacturing a micro-electromechanical device (10), in which are consecutively deposited on a substrate (1) a first electroconductive layer (2) in which an electrode (2A) is formed, a first electroinsulating layer (3) of a first material, a second electroinsulating layer (4) of a second material different from the first material, and a second electroconductive layer (5) in which a second electrode (5A) lying opposite the first electrode is formed which together with the first electrode (2A) and the first insulating layer (3) forms the device (10), in which after the second conductive layer (5) has been deposited, the second insulating layer (4) is removed by means of an etching agent which is selective with respect to the material of the second conductive layer (5). According to the invention for the first material and the second material materials are selected which are only limitedly selectively etchable with respect to each other and before depositing the second insulating layer (4) a further layer (6) is provided on top of the first insulating layer (3) of a further material that is selectively etchable with respect to the first material. In this way a silicon oxide and a silicon nitride may be applied for the insulating layers (3, 4) and thus the method according to the invention is very compatible with current IC processes. The second insulating layer (4) is preferably removed locally by etching, then the further layer (6) is completely removed by etching and, finally, the second insulating layer (4) is completely removed by etching.

WO 2004/037713 A1

nti Il Application No PCT/1B 03/04586

A. CLASSIFICATION OF SUBJECT MATTER IPC 7 B81C1/00

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

 $\begin{array}{ll} \mbox{Minimum documentation searched (classification system followed by classification symbols)} \\ \mbox{IPC 7} & \mbox{B81B} \end{array}$

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

INSPEC, EPO-Internal

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Further documents are listed in the continuation of box C.	χ Patent family members are listed in annex.
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Date of the actual completion of the international search 22 March 2004	Date of mailing of the International search report 30/03/2004
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016	Authorized officer Götz, A

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